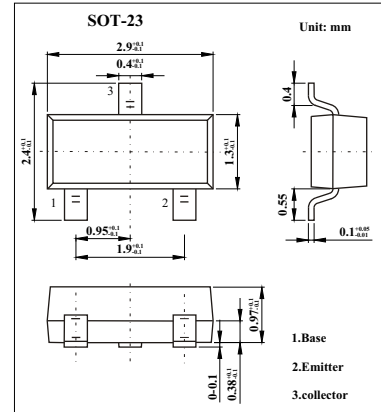


## NPN Switching Transistor KMBT2222A

### Features

High current (max. 600 mA)

Low voltage (max.40 V).



### Absolute Maximum Ratings $T_a = 25$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	75	V
Collector-emitter voltage	$V_{CEO}$	40	V
Emitter-base voltage	$V_{EBO}$	6	V
Collector current	$I_C$	600	mA
Total power dissipation $T_a = 25$	$P_{tot}$	300	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	417	K/W
Operating and Storage and Temperature Range	$T_j, T_{STG}$	-65 to +150	

## KMBT2222A

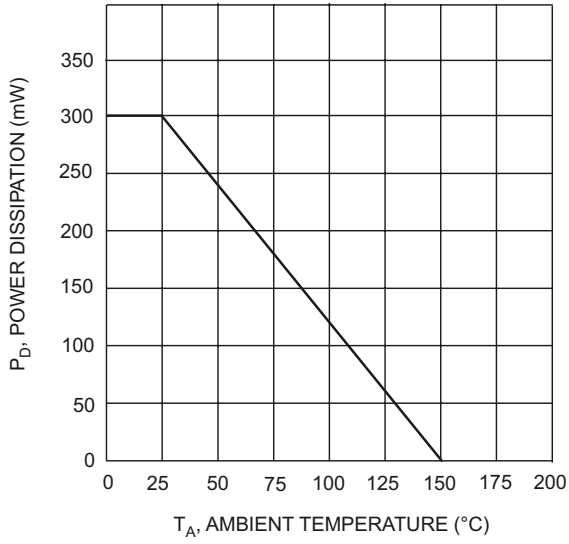
Electrical Characteristics  $T_a = 25$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10 \mu A, I_E = 0$	75			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	40			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C = 10 \mu A, I_C = 0$	6			V
Collector cutoff current	$I_{CBO}$	$I_E = 0; V_{CB} = 60 V$			10	nA
		$I_E = 0; V_{CB} = 60 V; T_J = 125$			10	$\mu A$
Emitter cutoff current	$I_{EBO}$	$I_C = 0; V_{EB} = 3 V$			10	nA
DC current gain	$h_{FE}$	$I_C = 0.1 mA; V_{CE} = 10 V$	35			
		$I_C = 1 mA; V_{CE} = 10 V$	50			
		$I_C = 10 mA; V_{CE} = 10 V$	75			
		$I_C = 10 mA; V_{CE} = 10 V; T_a = -55$	35			
		$I_C = 150 mA; V_{CE} = 10 V$	100		300	
		$I_C = 150 mA; V_{CE} = 1 V$	50			
collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 150 mA; I_B = 15 mA$			300	mV
		$I_C = 500 mA; I_B = 50 mA$			1	V
base-emitter saturation voltage	$V_{BEsat}$	$I_C = 150 mA; I_B = 15 mA$	0.6		1.2	V
		$I_C = 500 mA; I_B = 50 mA$			2	V
Delay time	$t_d$	$I_{B1} = 15 mA, I_C = 150 mA,$ $V_{CC} = 30V, V_{BE} = -0.5 V$			15	ns
Rise time	$t_r$				25	ns
Storage time	$t_s$	$I_{B1} = I_{B2} = 15 mA,$ $I_C = 150 mA, V_{CC} = 30V$			200	ns
Fall time	$t_f$				60	ns
Output Capacitance	$C_{obo}$	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$			8	pF
Input Capacitance	$C_{ibo}$	$V_{EB} = 0.5V, f = 1.0MHz, I_C = 0$			25	pF
Noise Figure	NF	$V_{CE} = 10 V, I_C = 100 \mu A, R_s = 1 k \Omega, f = 1 kHz$			4	dB
Transition frequency	$f_T$	$I_C = 20 mA; V_{CE} = 20 V; f = 100 MHz$	300			MHz

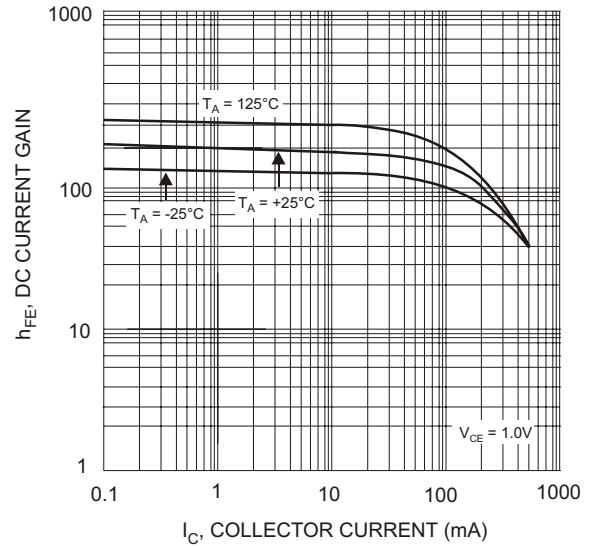
## Marking

Marking	1P
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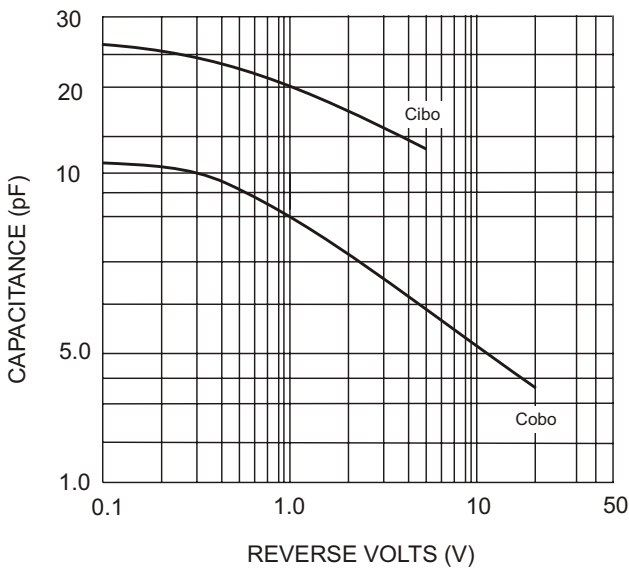
# KMBT2222A



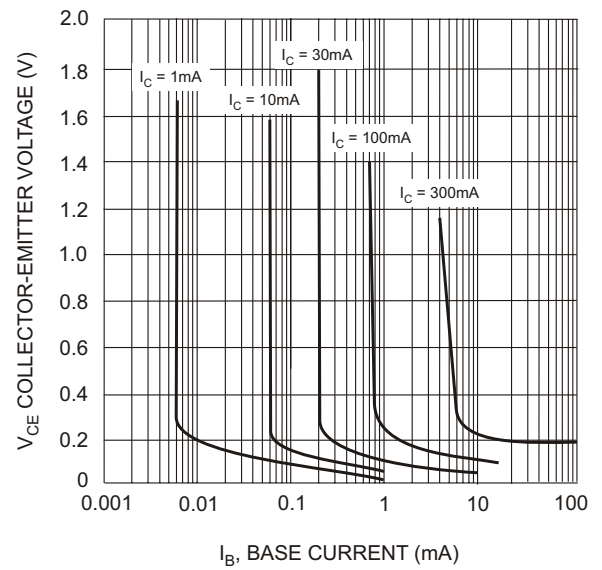
$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 1, Max Power Dissipation vs Ambient Temperature



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 2, Typical DC Current Gain vs Collector Current



REVERSE VOLTS (V)  
Fig. 3 Typical Capacitance



$I_B$ , BASE CURRENT (mA)  
Fig. 4 Typical Collector Saturation Region